



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

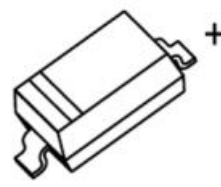
B5817W-B5819W

## SOD-123 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

SOD-123

### ■Features 特点

Low forward voltage drop 低正向压降  
 High current capability 高电流能力  
 Surface mount device 表面贴装器件  
 Case 封装:SOD-123



### ■Maximum Rating 最大额定值

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

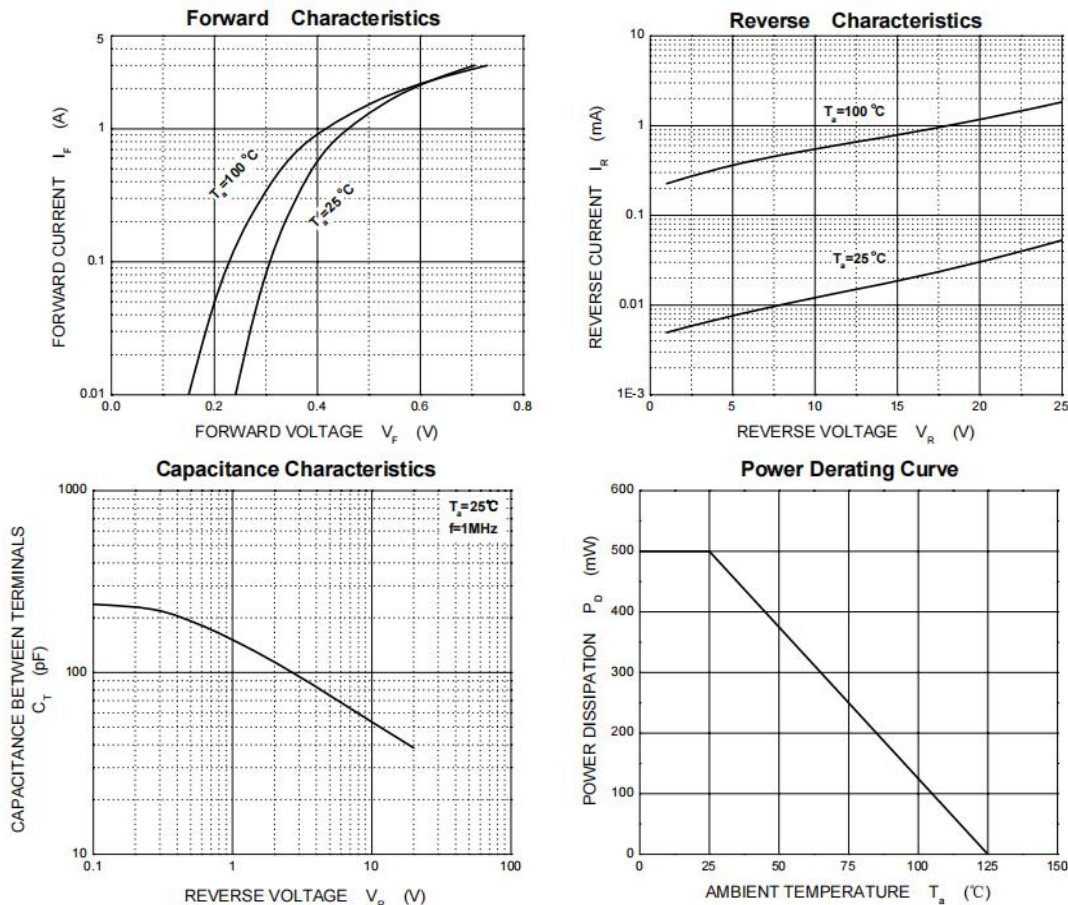
Characteristic 特性参数	Symbol 符号	B5817W	B5818W	B5819W	Unit 单位
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	20	30	40	V
DC Reverse Voltage 直流反向电压	$V_R$	20	30	40	V
RMS Reverse Voltage RMS 反向电压	$V_{R(RMS)}$	14	21	28	V
Forward Rectified Current 正向整流电流	$I_F$	1			A
Peak Surge Current 峰值浪涌电流	$I_{FSM}$	9			A
Repetitive Peak Surge Current 重复峰值浪涌电流	$I_{FRM}$	1.5			A
Power Dissipation 耗散功率	$P_D$	500			mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	250			$^{\circ}\text{C}/\text{W}$
Junction/Storage Temperature 结温/储藏温度	$T_J, T_{stg}$	-50to+150 $^{\circ}\text{C}$			$^{\circ}\text{C}$

### ■Electrical Characteristics 电特性

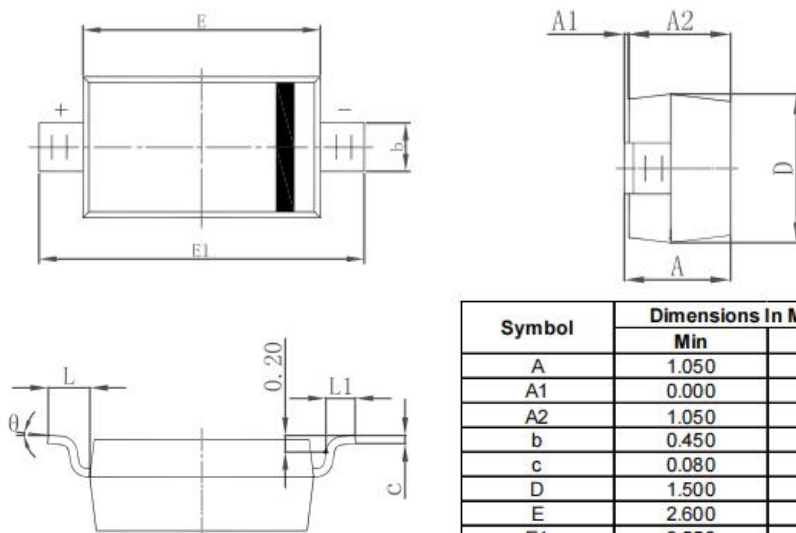
( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	B5817W	B5818W	B5819W	Unit 单位	Condition 条件
Reverse Voltage 反向电压	$V_R$	20	30	40	V	$I_R=1\text{mA}$
Forward Voltage 正向电压	$V_F$	0.45 0.75	0.55 0.875	0.6 0.9	V	$I_F=1\text{A}$ $I_F=3\text{A}$
Reverse Current 反向电流	$I_R$	1			mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	$C_T$	120			pF	$V_R=4\text{V}, f=1\text{MHz}$

## Typical Characteristic Curve 典型特性曲线



## Dimension 外形封装尺寸 SOD-123



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
$\theta$	0°		8°	